



DMN31D4UFZ

#### **Product Summary**

BV <sub>DSS</sub>	Rds(on) Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
30V	1.5Ω @ Vgs = 4.5V	0.31A
	2.0Ω @ Vgs = 2.5V	0.32A
	3.0Ω @ Vgs = 1.8V	0.26A
	4.5Ω @ V <sub>GS</sub> = 1.5V	0.21A

### Description

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- General purpose interfacing switches
- Power management functions
- Analog switches

#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features and Benefits**

- Low Package Profile, 0.4mm Maximum Package Height
- 0.62mm x 0.62mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

#### **Mechanical Data**

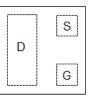
- Package: X2-DFN0606-3
- Package Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.001 grams (Approximate)





Bottom View

Diode 5 Equivalent Circuit



Top View Package Pin Configuration

#### Ordering Information (Note 4)

Part Number	Backaga	Packing		
	Package	Qty.	Carrier	
DMN31D4UFZ-7B	X2-DFN0606-3	10k	Tape & Reel	

G

Gate Protect

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

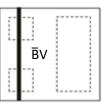
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**

Notes:



 $\overline{B}V$  = Product Type Marking Code Bar Denotes Gate and Source Side

Top View



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	30	V		
Gate-Source Voltage	Vgss	±12	V		
Continuous Drain Current (Note 5) $V_{GS} = 4.5V$	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +85°C	ID	0.31 0.2	А
Pulsed Drain Current (Note 6)	Ідм	0.7	A		

### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	PD	0.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	403	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage		BVDSS	30	—	—	V	Vgs = 0V, ID = 250µA	
Zero Gate Voltage Drain Current	Tc = +25°C	IDSS	_		100	nA	VDS = 24V, VGS = 0V	
Gate-Source Leakage		Igss	_		±10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage		V <sub>GS(TH)</sub>	0.4		1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
			_	1.3	1.5		$V_{GS} = 4.5V, I_{D} = 100mA$	
Static Drain-Source On-Resistance		Descent	_	1.6	2.0	Ω	$V_{GS} = 2.5V, I_D = 50mA$	
Static Drain-Source On-Resistance		RDS(ON)	—	1.8	3.0		$V_{GS} = 1.8V, I_D = 20mA$	
			—	2.0	4.5		$V_{GS} = 1.5V, I_D = 10mA$	
Diode Forward Voltage		Vsd	_	0.54	1.0	V	$V_{GS} = 0V$ , $I_{S} = 10mA$	
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance		Ciss	—	15.4	—	pF		
utput Capacitance		Coss	—	8	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Reverse Transfer Capacitance		Crss	_	5	—	pF		
Total Gate Charge		Qg	_	0.3	_	nC		
Gate-Source Charge		Qgs	—	0.05	—	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ ID = 200mA	
Gate-Drain Charge		Qgd	_	0.1	—	nC		
Turn-On Delay Time		tD(ON)	_	5.7	—	ns		
Turn-On Rise Time		t <sub>R</sub>	_	9.1	—	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time		t <sub>D(OFF)</sub>	_	146	—	ns	$R_G = 2\Omega$ , $I_D = 200mA$	
Turn-Off Fall Time		tF	_	48	_	ns		

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

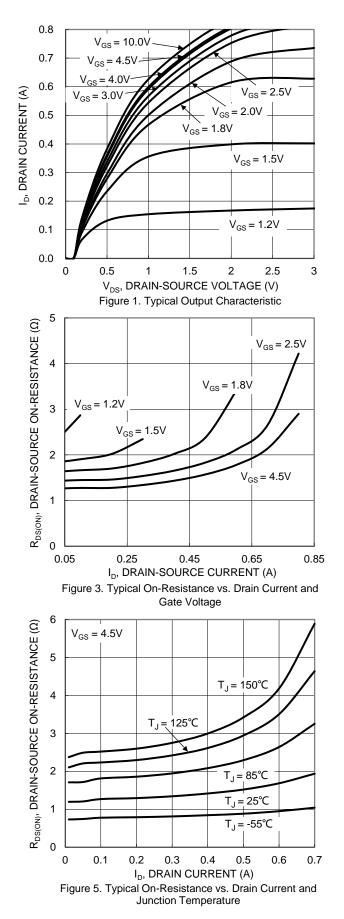
6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

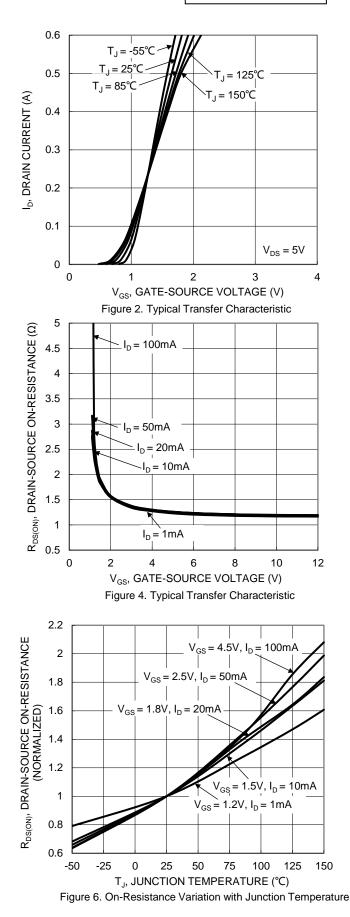
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

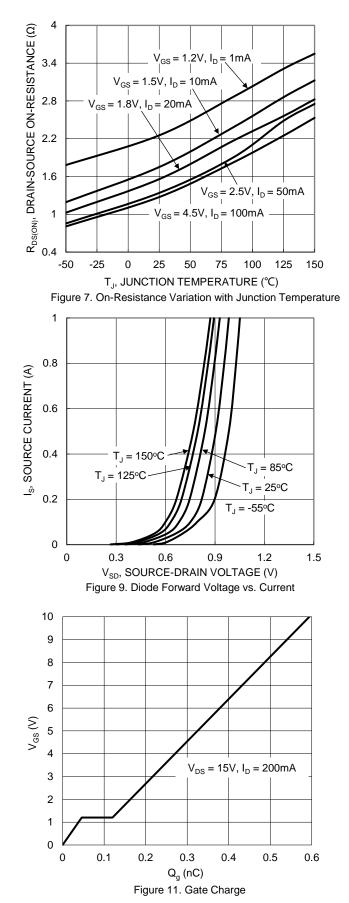


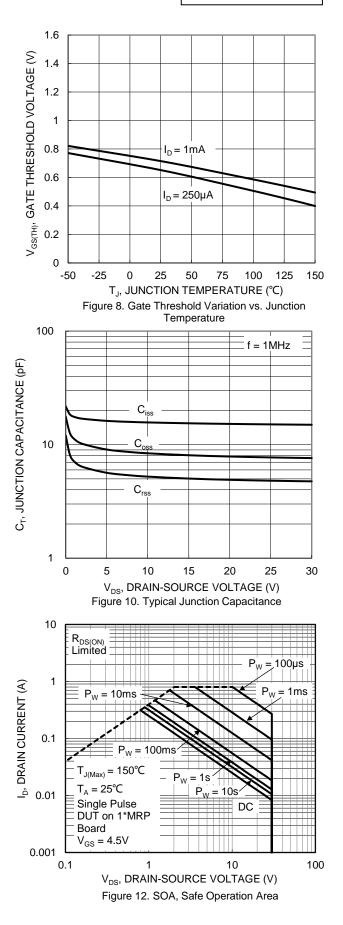
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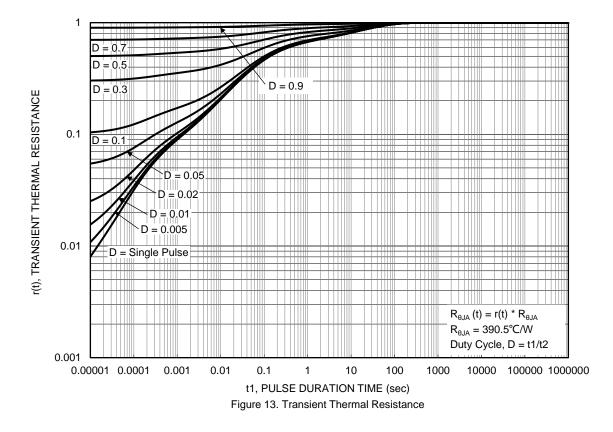








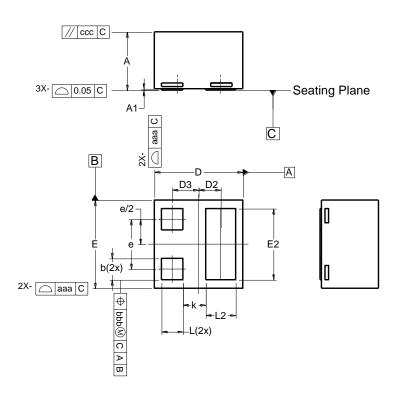






### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



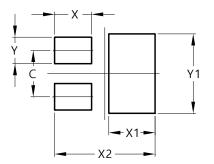
X2-DFN0606-3   Dim Min Max Typ   A 0.36 0.40 0.39   A1 0.00 0.05 0.02   b 0.10 0.20 0.15   D 0.57 0.67 0.62   D2 0.155 BSC   D3 0.185 BSC   E 0.57 0.67 0.62   E2 0.40 0.60 0.50   e 0.35 BSC K				
A 0.36 0.40 0.39   A1 0.00 0.05 0.02   b 0.10 0.20 0.15   D 0.57 0.67 0.62   D2 0.155 BSC   D3 0.185 BSC   E 0.57 0.67 0.62   E2 0.40 0.60 0.50   e 0.35 BSC				
A1 0.00 0.05 0.02   b 0.10 0.20 0.15   D 0.57 0.67 0.62   D2 0.155 BSC D3 0.185 BSC   E 0.57 0.67 0.62   E2 0.40 0.60 0.50   e 0.35 BSC				
b 0.30 0.30 0.30   b 0.10 0.20 0.15   D 0.57 0.67 0.62   D2 0.155 BSC   D3 0.185 BSC   E 0.57 0.67 0.62   E2 0.40 0.60 0.50   e 0.35 BSC				
D 0.57 0.67 0.62   D2 0.155 BSC   D3 0.185 BSC   E 0.57 0.67 0.62   D3 0.185 BSC   E 0.57 0.67 0.62   E2 0.40 0.60 0.50   e 0.35 BSC				
D2 0.157 0.02   D3 0.185 BSC   E 0.57 0.67 0.62   E2 0.40 0.60 0.50   e 0.35 BSC				
D3 0.185 BSC   E 0.57 0.67 0.62   E2 0.40 0.60 0.50   e 0.35 BSC				
E 0.57 0.67 0.62   E2 0.40 0.60 0.50   e 0.35 BSC				
E2 0.40 0.60 0.50   e 0.35 BSC				
e 0.35 BSC				
k 0.16 REE				
N U.IUKLE				
L 0.10 0.20 0.15				
L2 0.11 0.31 0.21				
<b>aaa</b> 0.08				
<b>bbb</b> 0.07				
<b>CCC</b> 0.05				
All Dimensions in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-DFN0606-3

X2-DFN0606-3



Dimensions	Value (in mm)
С	0.350
Х	0.280
X1	0.350
X2	0.760
Y	0.200
Y1	0.600



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